



# AMP6035P SOLID STATE PULSE HIGH POWER AMPLIFIER

## FEATURES

- High power GaN pulse devices
- Suitable for X-Band linear pulse applications
- Built-in Ethernet Control and Protection circuits
- Rack mounted chassis
- High reliability and ruggedness



## ELECTRICAL SPECIFICATIONS

Parameter	Specification			Notes
Operating Frequency Range	9.7 - 9.9 GHz			
Peak Output Power	4000 Watt Min			
Input Power	0 dBm Nom			Pulsed
Saturated Gain	66 dB Min			
Pulse Characteristics	<b>Duty</b>	<b>Width</b>	<b>PRF</b>	PRF relative to DS & PW @ 50 $\mu$ Sec
	10 % Max	0.2 - 50 $\mu$ Sec	18 KHz Max	
Pulse Droop	0.7 dB Max			
Rise / Fall Time	50 nSec			
Input / Output VSWR	1.5 : 1			Relative to 50 Ohm
Harmonics	-20 dBc Max			
Out of Band Spurious levels	-50 dBc Max			Mon-harmonic or Gaussian
Load VSWR Protection	2.5 : 1			Without damage
Gate Control Inputs	TTL - gating pulse must precede RF by 2 $\mu$ Sec			
AC Input Voltage	180 - 260 VAC, 50-60 Hz			
Efficiency	15 % Min			
RF Output Sample	-60 dB Nom			

## ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50°C	
Vibrations	MIL-STD 810G, Method 514.6	
Altitude	10,000 feet	30,000 feet non-operating

## MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	Preliminary drawing	7U, 19" rack
Weight	TBD	
RF Input Connector	SMA (F) Jack	
RF Output Connector	WR-112 Waveguide flange	Waveguide pressure sensor
RF Sample Port	SMA (F) Jack	
AC Power	MS3122E14-5P	or similar
Transmit Gating Connector	MS circular or similar	
Monitor & Control	Ethernet RJ-45 circular connector TCP/IP RS422/485 D-sub 9S port for redundancy	
Cooling	Built in Fan Cooling	Front Inlet, Rear outlet
Elapse Hour Meter	Internally tracked via software	Ethernet status message

## OUTLINE DRAWING

